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60V +175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C
60V	$27m\Omega @ V_{GS} = 10V$	22.6A
60 V	30mΩ @ V _{GS} = 6V	21.5A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

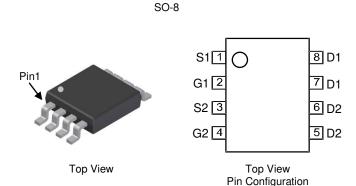
- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

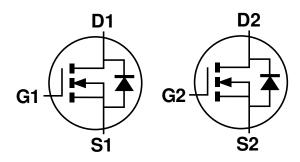
Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_g Minimizes Switching Losses
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.074 grams (Approximate)





Equivalent Circuit

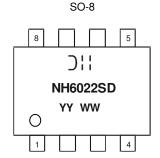
Ordering Information (Note 5)

Part Number	Case	Packaging
DMNH6022SSDQ-13	SO-8	2,500 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Oll = Manufacturer's Marking
NH6022SD = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 16 = 2016)
WW = Week (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	60	V	
Gate-Source Voltage	V_{GSS}	±20	V	
Centing our Drain Current / 10// (Note 7)	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I _D	22.6 16.0	А
Continuous Drain Current V _{GS} = 10V (Note 7)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	7.1 5.9	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	45	Α	
Maximum Continuous Body Diode Forward Current (Note 7)	Is	2	Α	
Avalanche Current L = 0.1mL (Note 8)	I _{AS}	22	Α	
Avalanche Energy L = 0.1mL (Note 8)	E _{AS}	24	mJ	

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	104	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{ heta JA}$	60	
Total Power Dissipation (Note 7)	T _A = +25°C	P _D	2.1	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	Do.,	74	°C/W
Thermal nesistance, sunction to Ambient (Note 1)	t<10s	$R_{ heta JA}$	42	
Thermal Resistance, Junction to Case (Note 7)	$R_{ heta JC}$	7.25		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

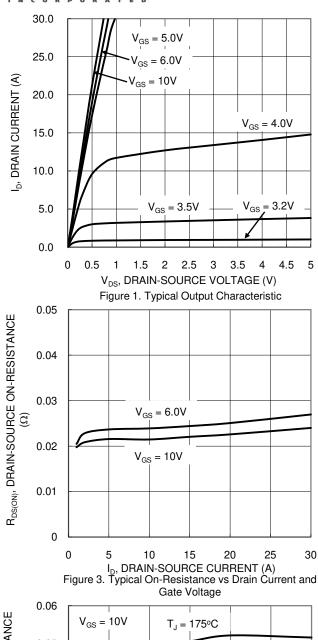
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	1.0	_	3.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance			21	27	mΩ	$V_{GS} = 10V, I_D = 5A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	24	30	11177	$V_{GS} = 6V, I_{D} = 5A$	
Diode Forward Voltage	V_{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_S = 1.7A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	1	2127	_	рF	V 05V V 0V	
Output Capacitance	Coss	1	86	_	pF	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	54	_	pF	1 = 1.000112	
Gate Resistance	R_{g}	_	2.0	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge at (V _{GS} = 10V)	Q_g	_	32	_	nC		
Total Gate Charge at (V _{GS} = 4.5V)	Q_g	_	14	_	nC	V 20V I 6A	
Gate-Source Charge	Q_{gs}	_	7	_	nC	$V_{DS} = 30V, I_D = 6A$	
Gate-Drain Charge	Q_{gd}	_	4	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	5.4	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$ $R_{G} = 6\Omega, I_{D} = 1A$	
Turn-On Rise Time	t _R	_	4.4	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	30.4	_	ns		
Turn-Off Fall Time	t _F	_	8.4	_	ns	7	
Body Diode Reverse Recovery Time	t _{RR}	_	18.1	_	ns	I _F = 1.7A, di/dt = 100A/μs	
Body Diode Reverse Recovery Charge	Q _{RR}		12.5	_	nC	$I_F = 1.7A$, $di/dt = 100A/\mu s$	

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
- 8. Ias and Eas rating are based on low frequency and duty cycles to keep $T_J = +25$ °C.
- 9. Short duration pulse test used to minimize self-heating effect.

 10. Guaranteed by design. Not subject to product testing.







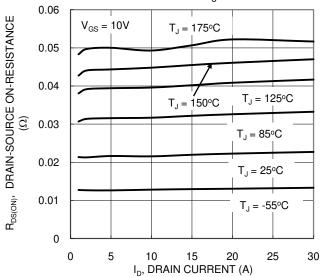
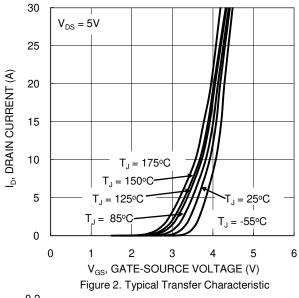
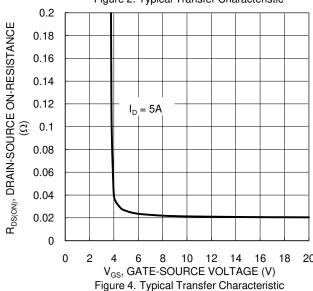


Figure 5. Typical On-Resistance vs Drain Current and Junction Temperature





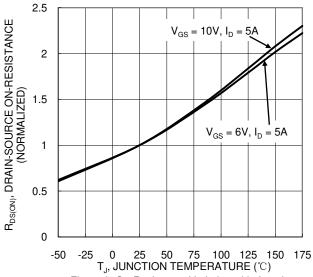


Figure 6. On-Resistance Variation with Junction Temperature





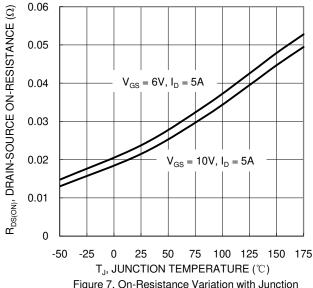


Figure 7. On-Resistance Variation with Junction Temperature

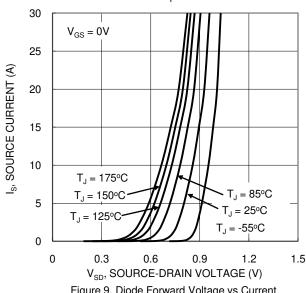
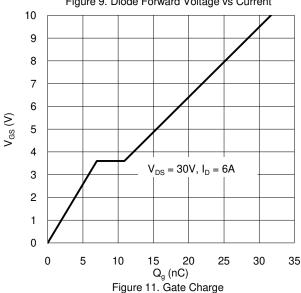


Figure 9. Diode Forward Voltage vs Current



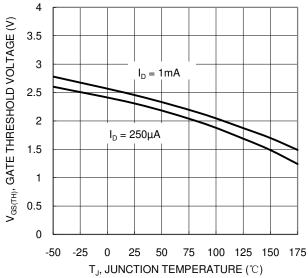


Figure 8. Gate Threshold Variation vs Junction Temperature

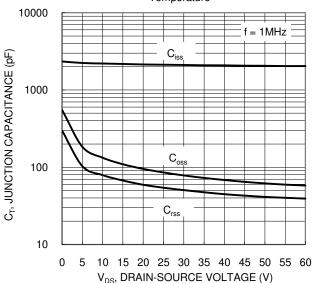
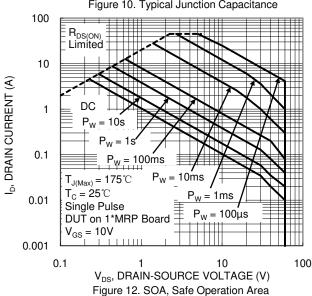


Figure 10. Typical Junction Capacitance





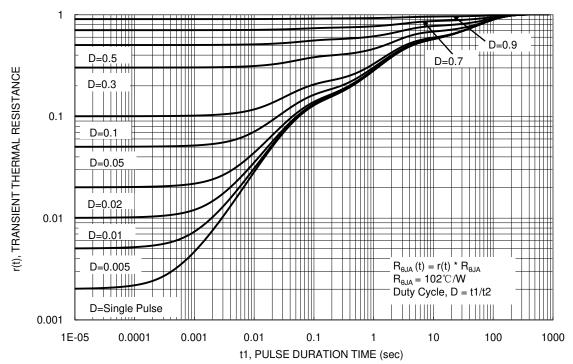


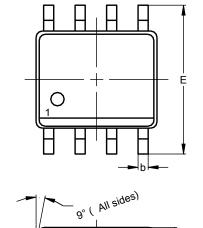
Figure 13. Transient Thermal Resistance

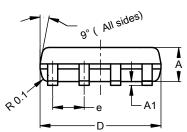


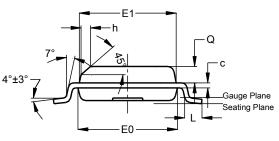
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8





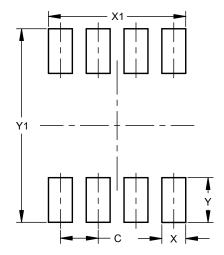


SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A 1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
С	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Е	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е			1.27		
h	-		0.35		
L	0.62	0.82	0.72		
Q	0.60	0.70	0.65		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



Dimensions	Value (in mm)			
С	1.27			
Х	0.802			
X1	4.612			
Υ	1.505			
Y1	6.50			



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